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Fig. 1

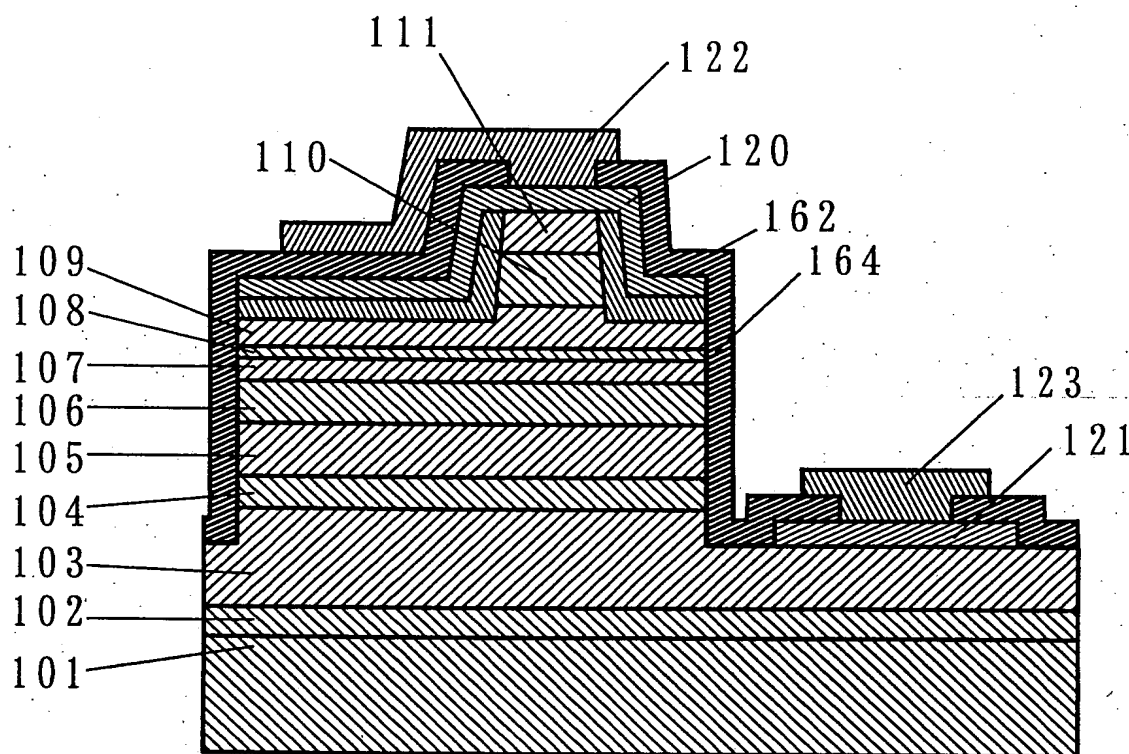




Fig. 2

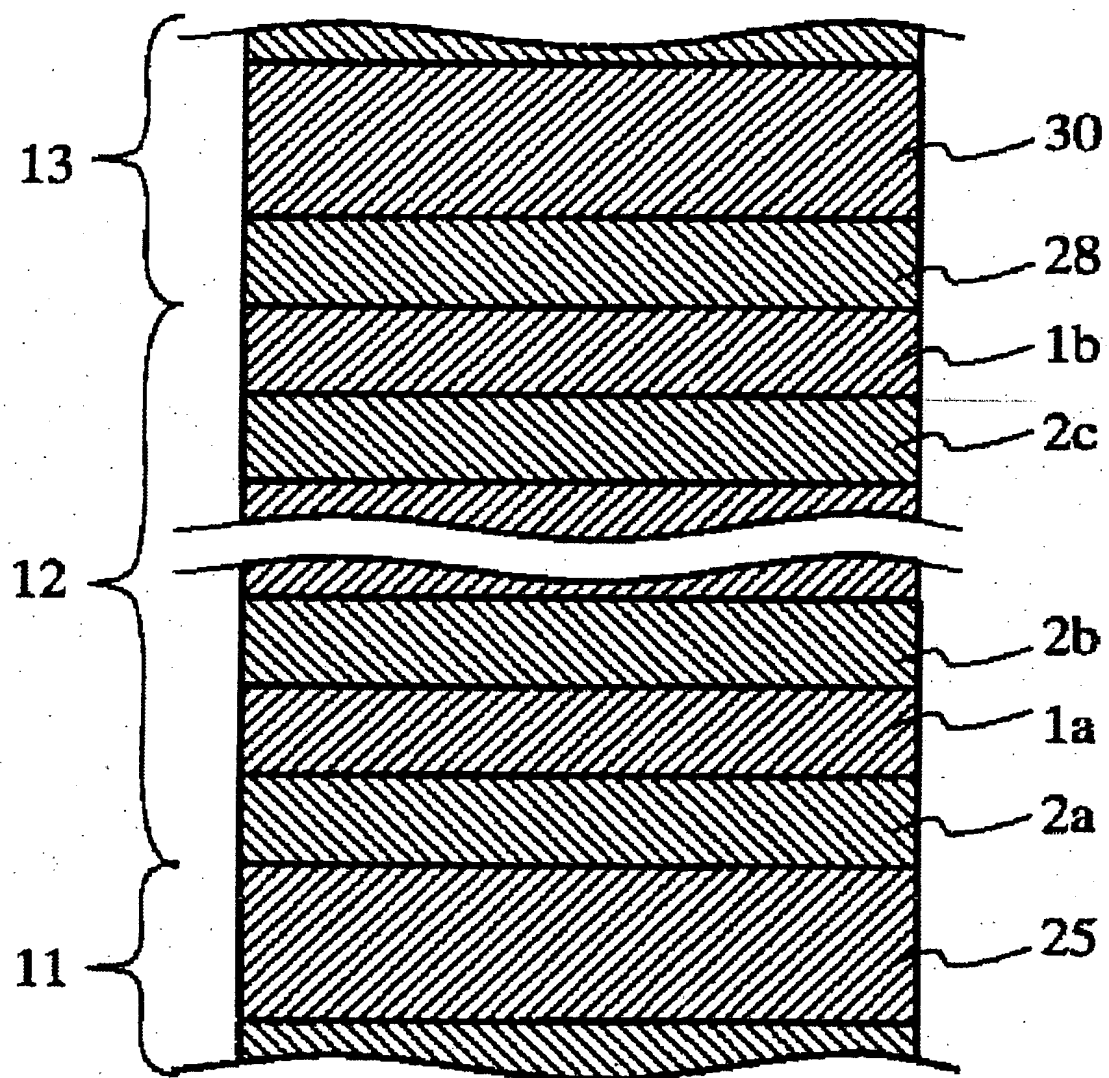




Fig. 3

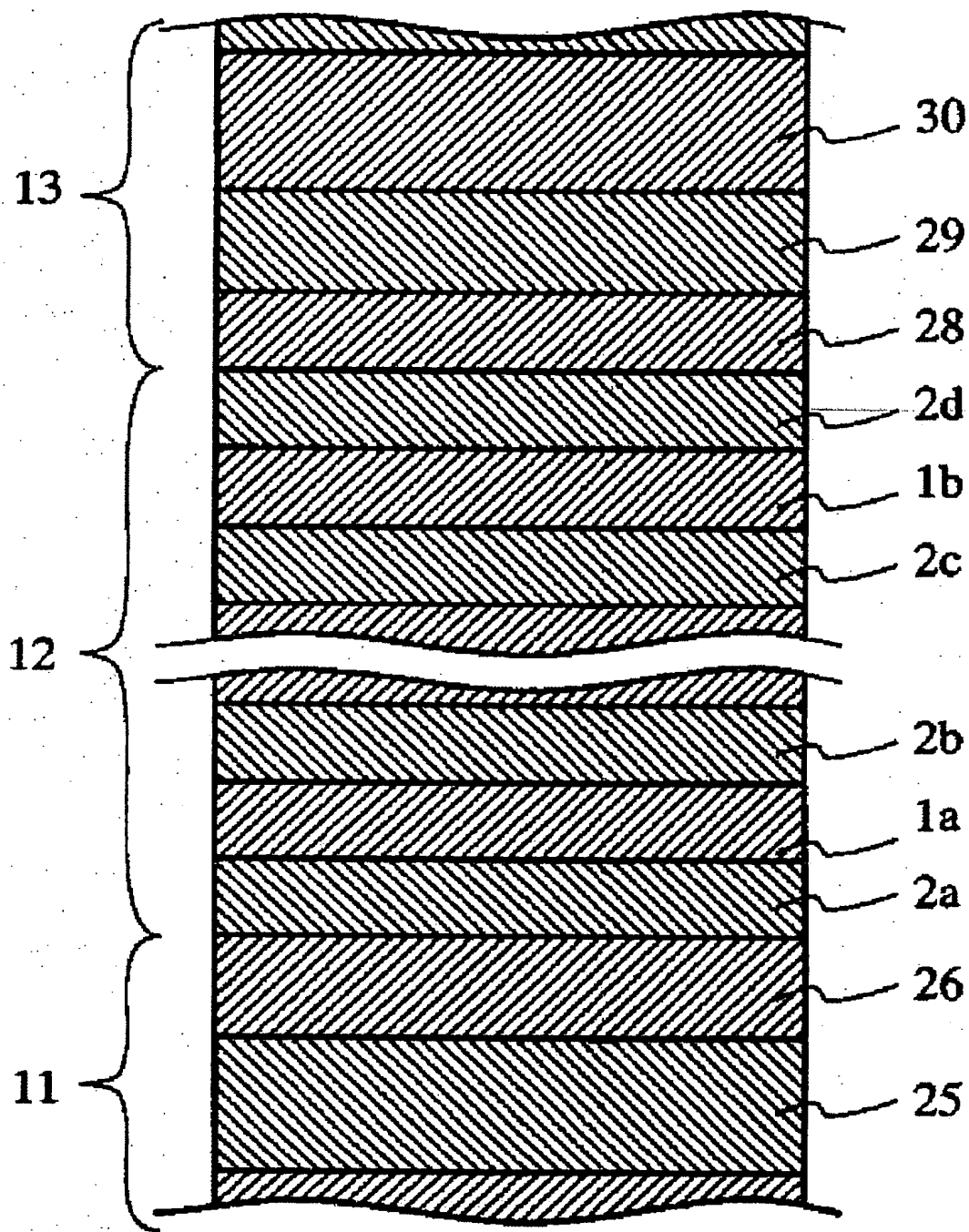




Fig. 4

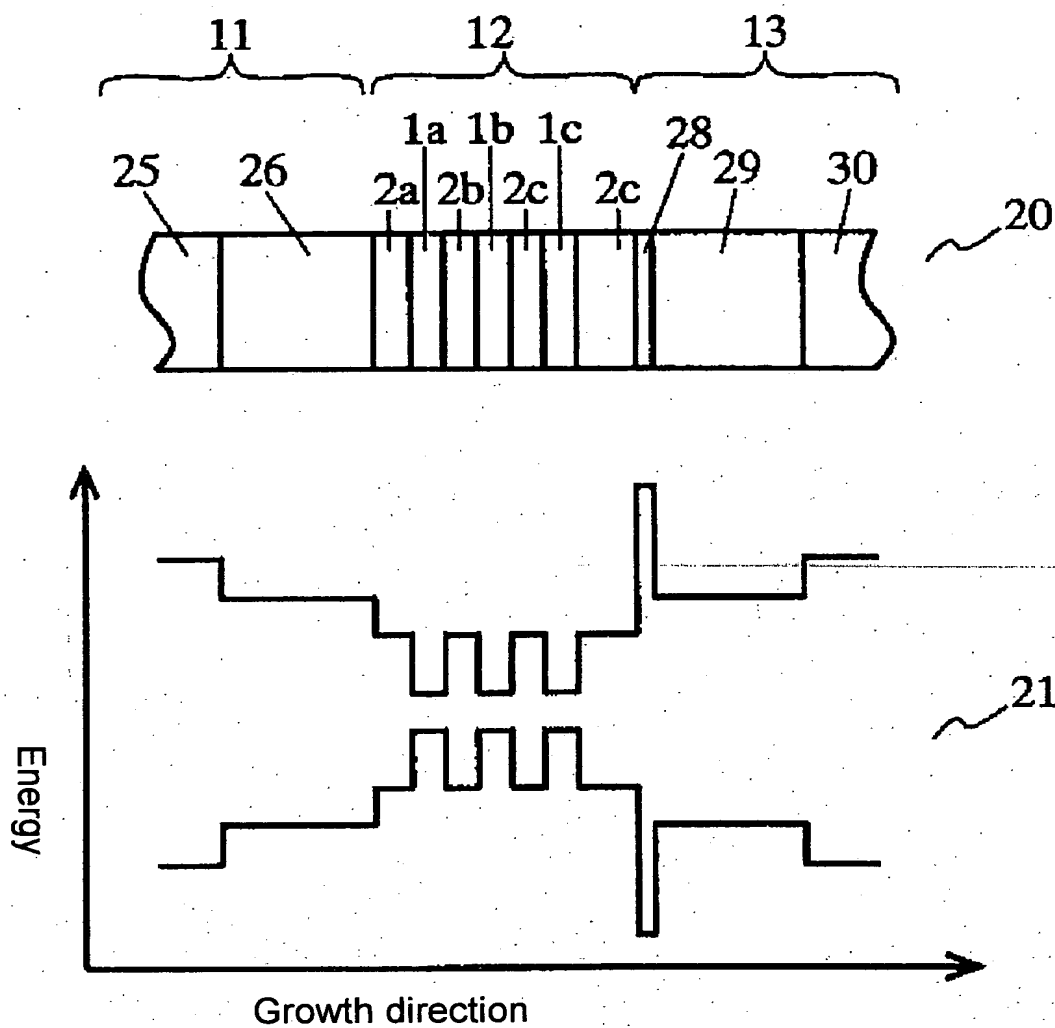
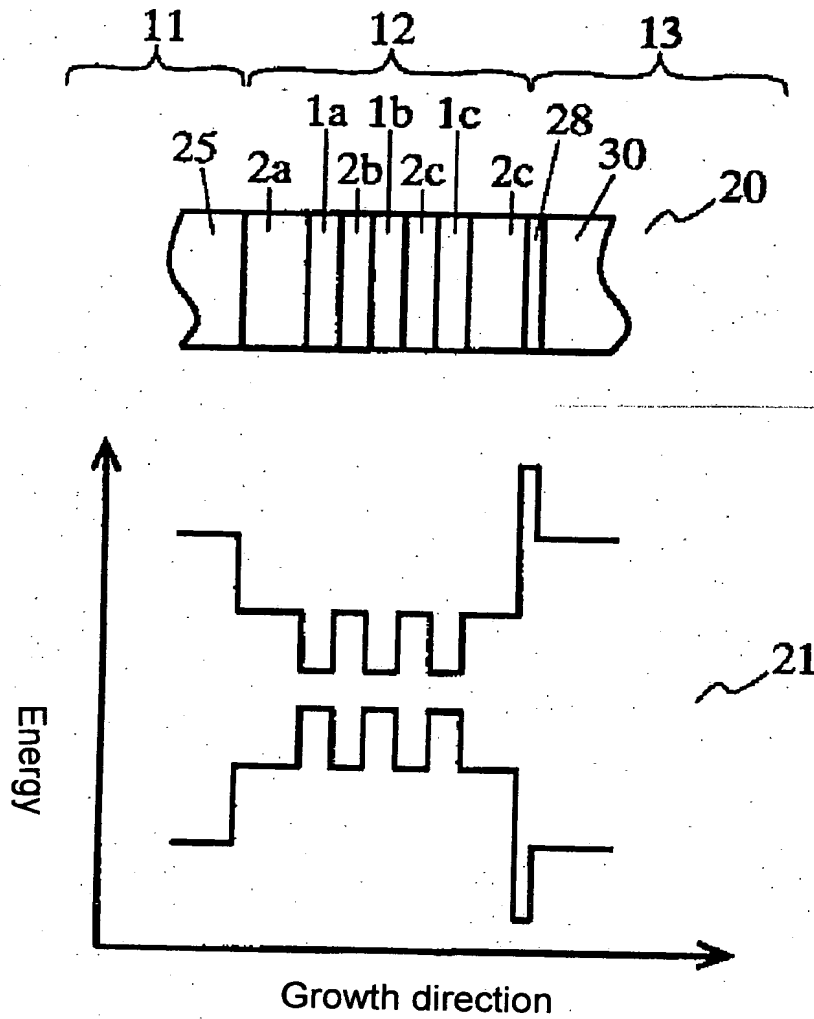




Fig. 5



The top diagram shows a cross-sectional view of a semiconductor device structure 20. It consists of a substrate 25 with a top layer 26. A central region contains a stack of layers: 2a, 1a, 2b, 1b, 2c, and 28. This central stack is flanked by regions 29 and 30. The structure is divided into three main sections labeled 11, 12, and 13. Section 11 includes layers 25 and 26. Section 12 includes layers 2a, 1a, 2b, 1b, and 2c. Section 13 includes layers 28, 29, and 30. The bottom diagram is an energy band diagram 21 showing Energy versus Growth direction. It illustrates the energy levels of the various layers in the structure, showing how the energy bands change across the different regions and layers.



Fig. 7

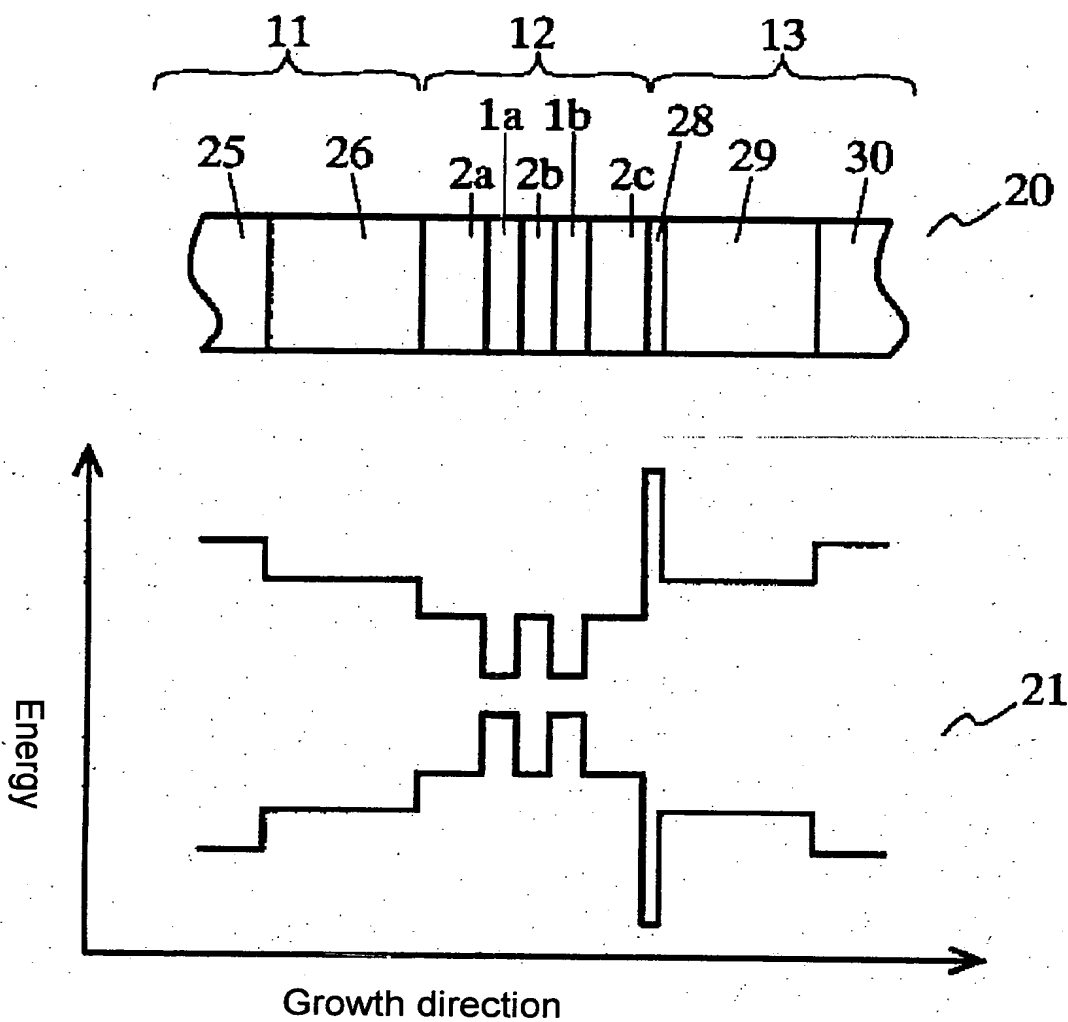




Fig. 8A

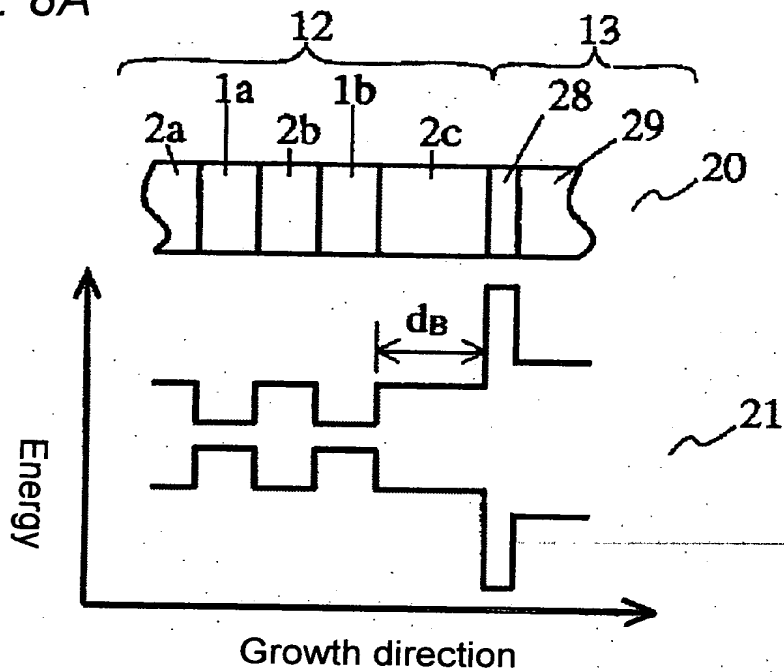


Fig. 8B

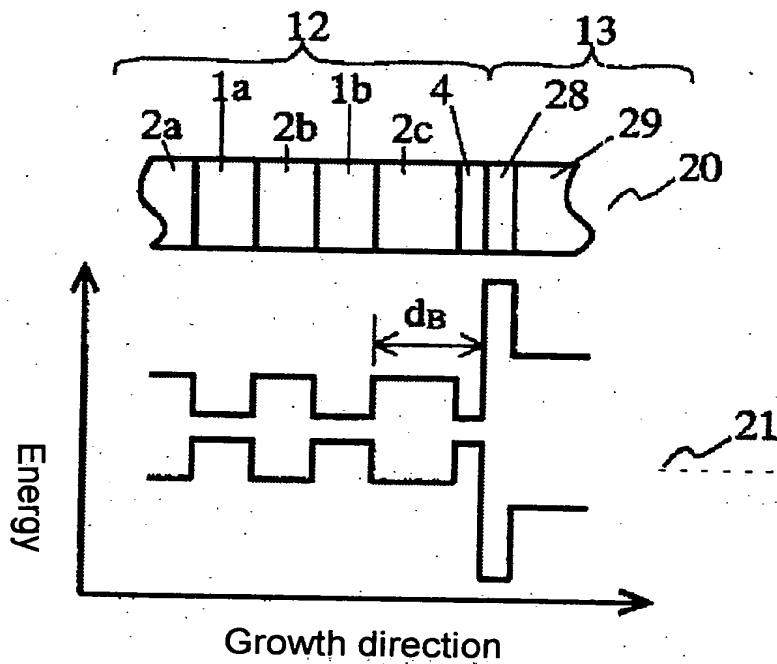




Fig. 9A

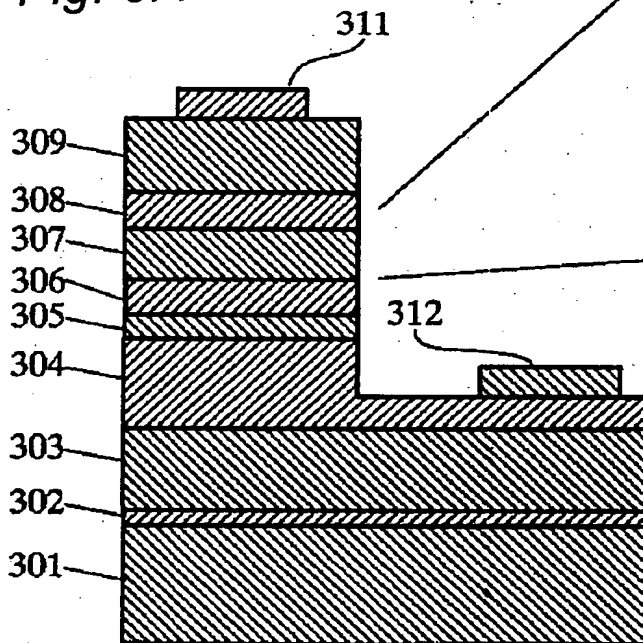


Fig. 9B

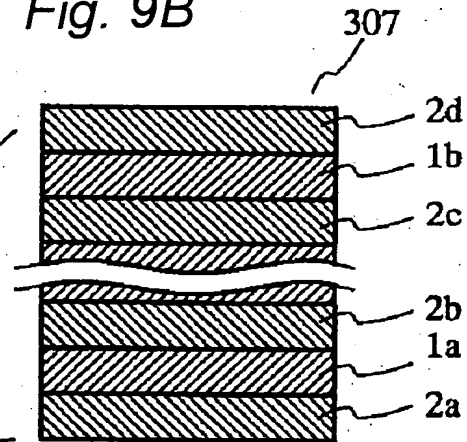




Fig. 10

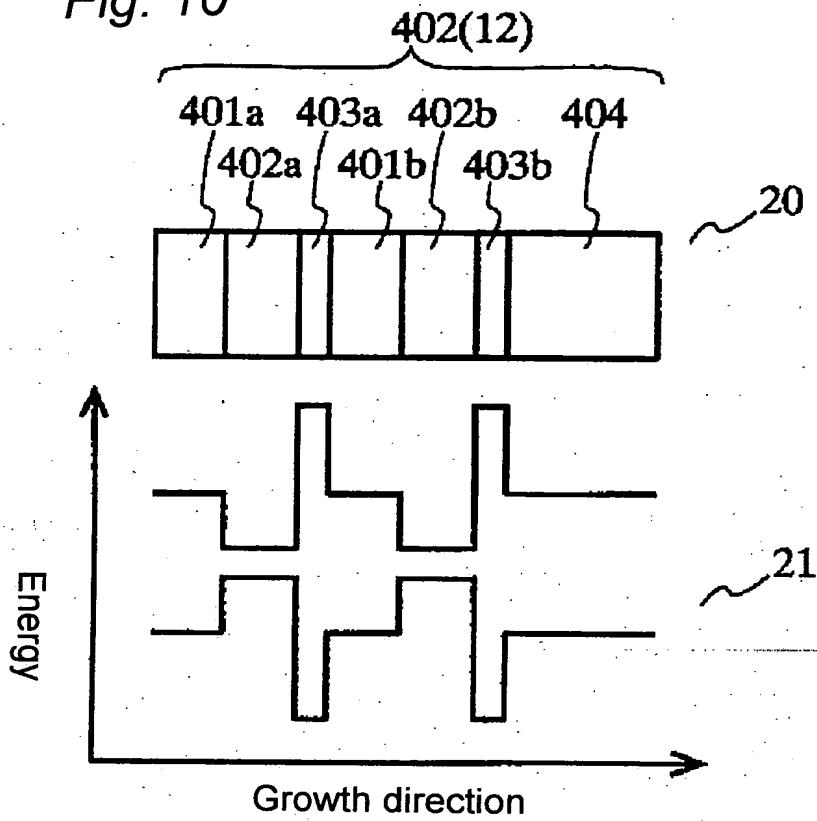


Fig. 11

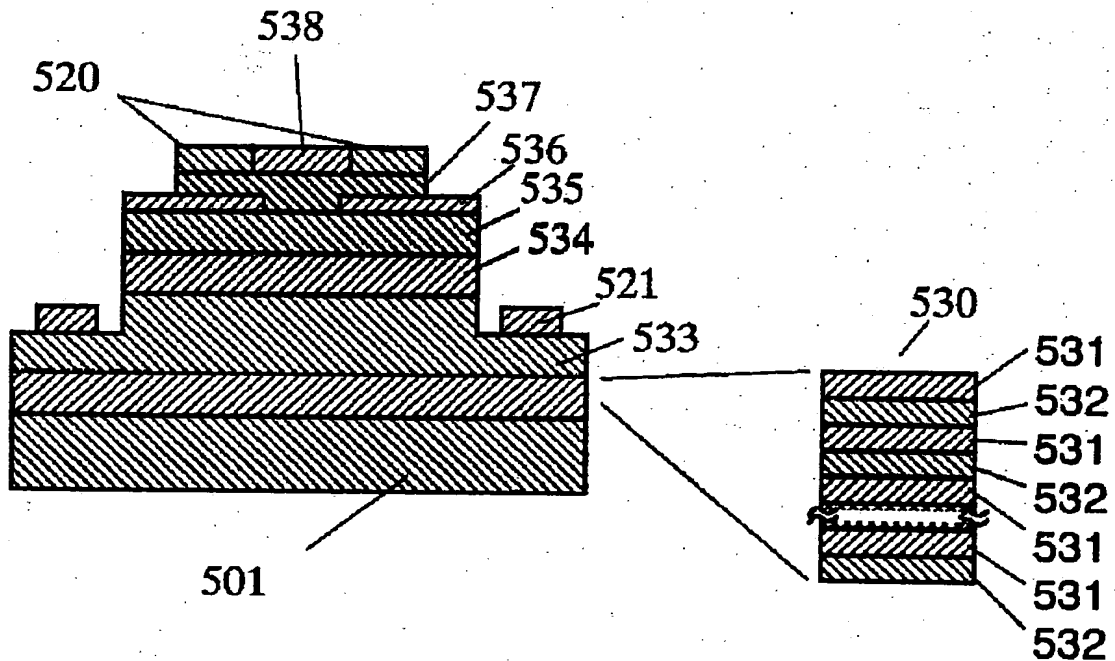




Fig. 12

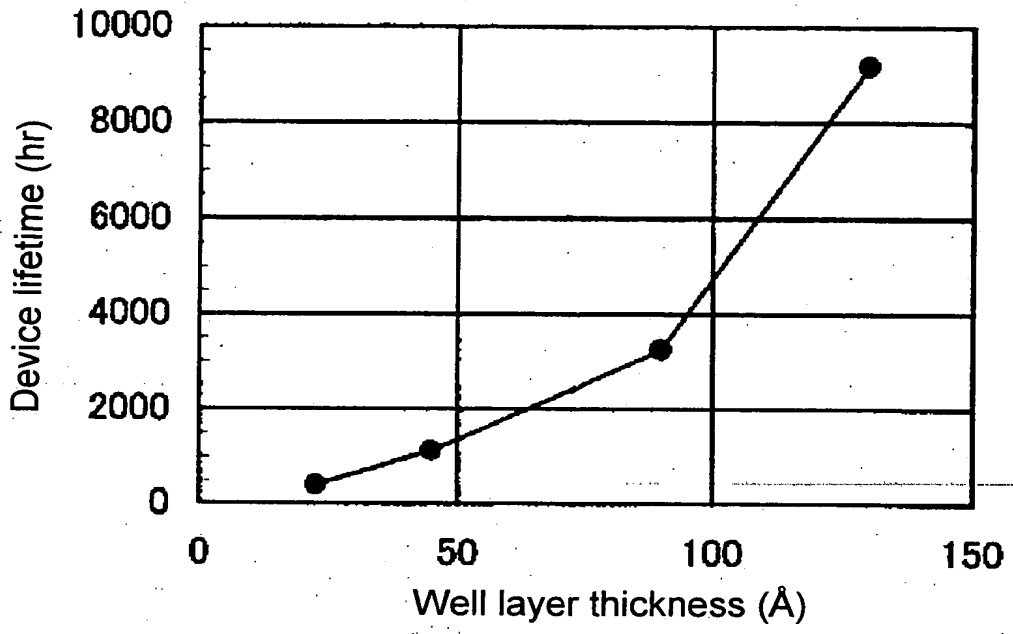


Fig. 13

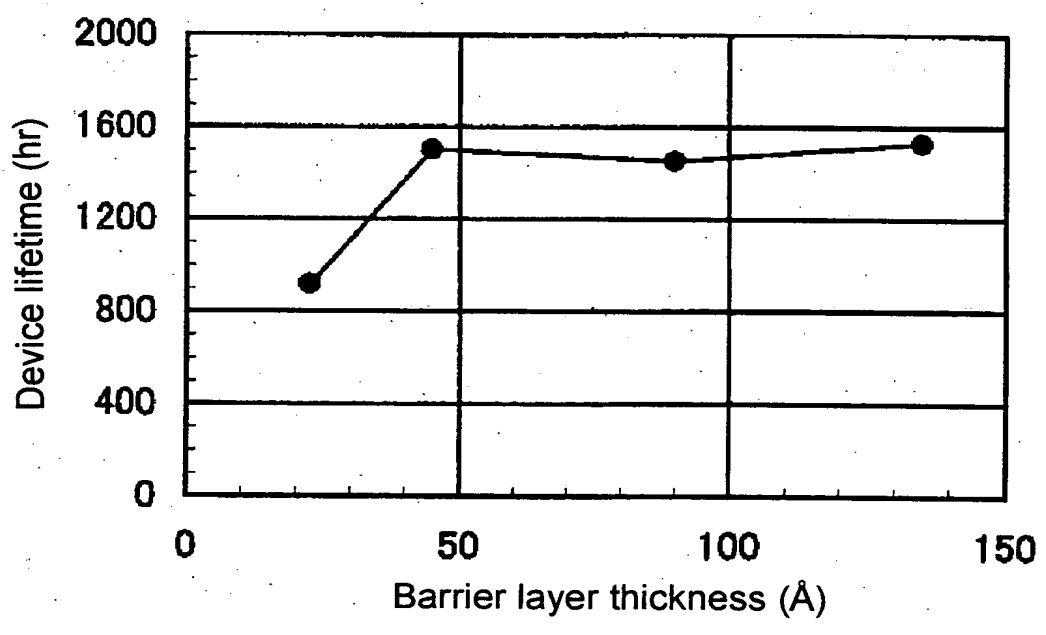




Fig. 14

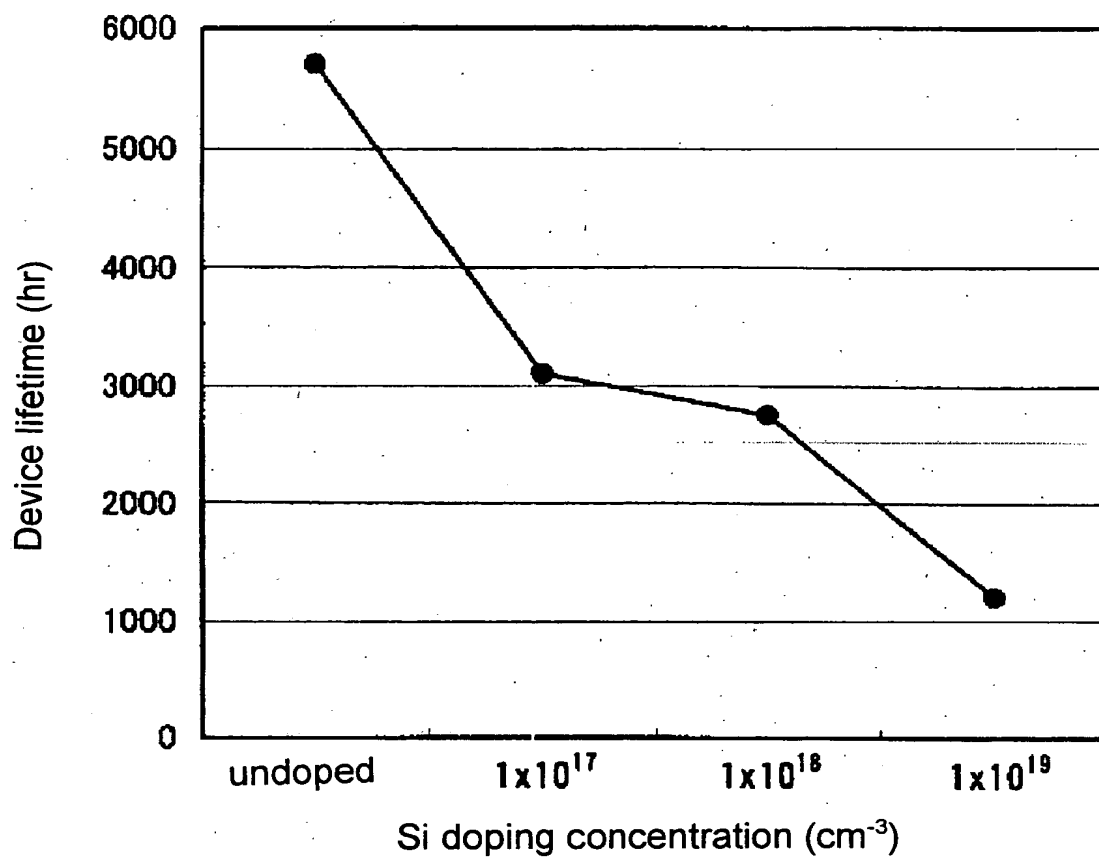




Fig. 15

